BAT54WT thru BAT54SWT

Schottky Barrier Diode

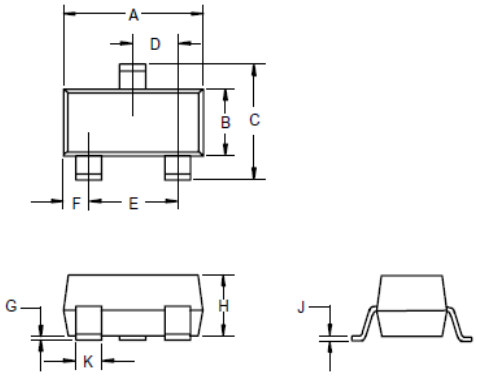
REVERSE VOLTAGE - **30** Volts
POWER DISSIPATION - **20** mW

FEATURES

- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1
- Low Forward Voltage
- Surface Mount SOT-323 Package
- Capable of 200mWatts of Power Dissipation
- Lead Free Finish/Rohs Compliant ("P"Suffix designates RoHS Compliant. See ordering information)

Part Number	Device Marking	Type	Pin Configuration
BAT54WT	KL5	Single	Figure 1
BAT54AWT	KL6	Dual	Figure 2
BAT54CWT	KL7	Dual	Figure 3
BAT54SWT	KL8	Dual	Figure 4

SOT-323



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.071	.087	1.80	2.20	
B	.045	.053	1.15	1.35	
C	.079	.087	2.00	2.20	
D	.026 Nominal		0.65Nominal		
E	.047	.055	1.20	1.40	
F	.012	.016	.30	.40	
G	.000	.004	.000	.100	
H	.035	.039	.90	1.00	
J	.004	.010	.100	.250	
K	.012	.016	.30	.40	

Dimensions in inches and (millimeters)

Absolute Maximum Ratings (T_A = 25 °C)

Parameter	Symbol	Values	Unit
Continuous Reverse Voltage	V_R	30	V
Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	300	mA
Non-Repetitive Peak Forward Current t<1s	I_{FSM}	600	mA
Total Power Dissipation @ TA = 25°C	P_D	200	mW
Junction temperature	T_J	-55 to +125	℃
Storage temperature range	T_{STG}	-55 to +125	℃

Characteristics at T_A = 25 °C

Parameter	Symbol	Values	Unit
Reverse Breakdown voltage	$V_{(BR)}$	30	V
Reverse current V_R = 25 V	I_R	2	uA
Forward voltage I_F = 0.1 m	V_F	240	mV
I_F =1mA		320	
I_F =10m		400	
I_F = 30m		500	
I_F = 100		1000	
Total capacitance V_R = 1V, f = 1 MHz	C_J	10	pF
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	500	K/W
Reverse Recovery Time at I_F=I_R=10mA,I_{RR}=0.1*I_R,R_L=100Ω	T_{RR}	5	ns

REV. 1, 19-Jan-2016

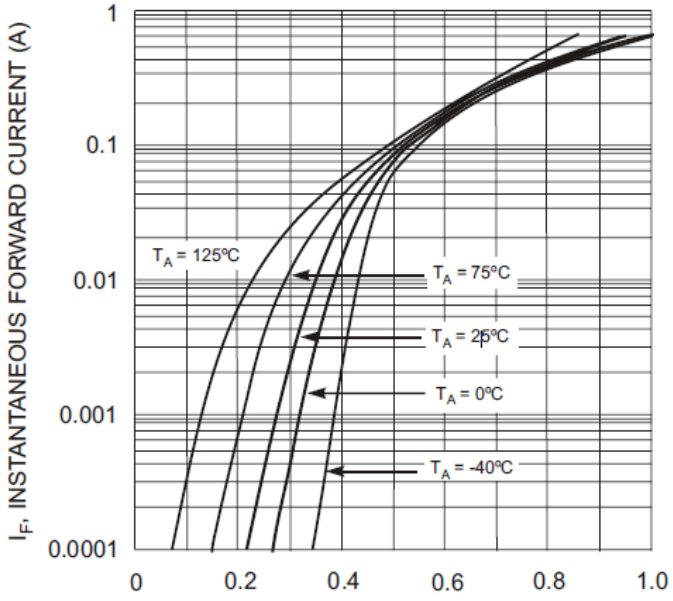


Fig. 1 Forward Characteristics

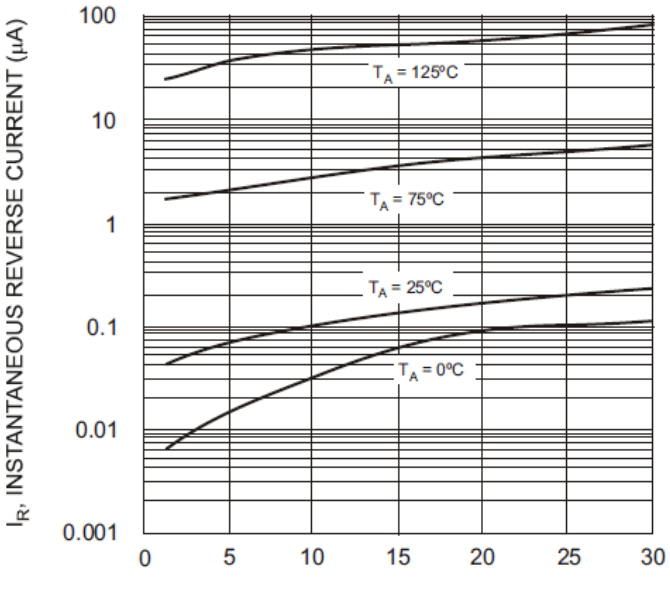


Fig. 2 Typical Reverse Characteristics

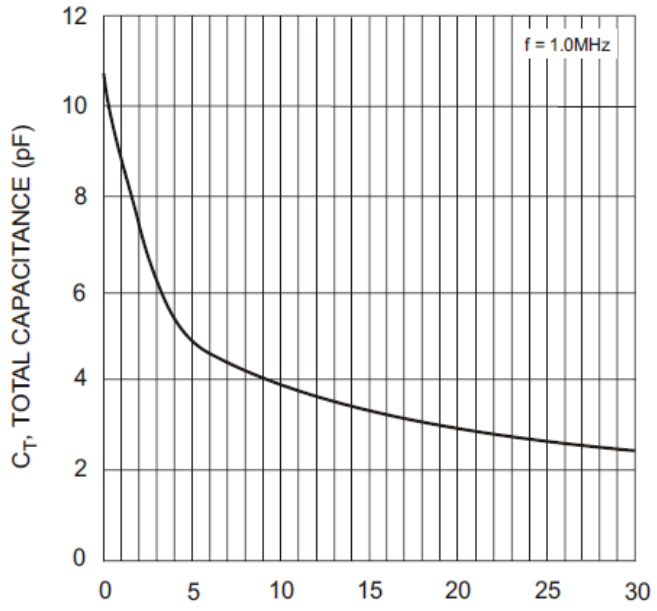


Fig. 3 Typical Capacitance vs. Reverse Voltage

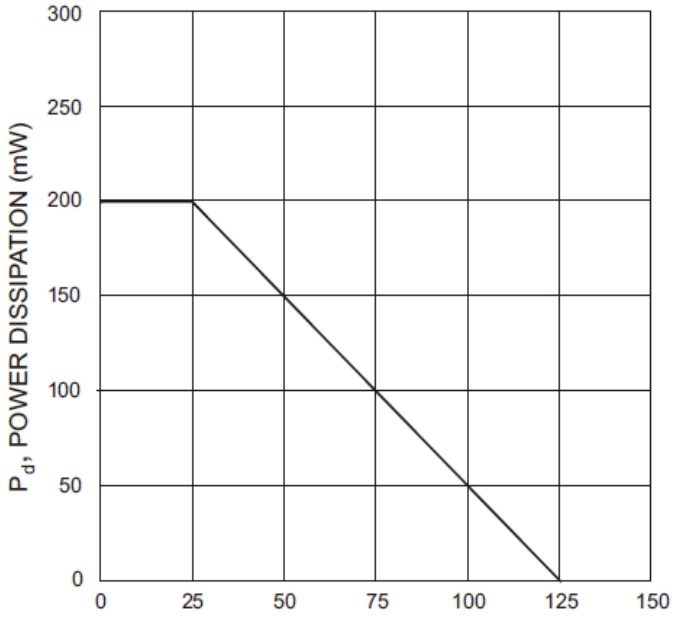


Fig. 4 Power Derating Curve

Pin Configuration - Top View

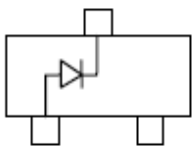


Figure 1

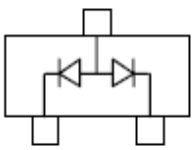


Figure 2

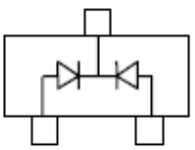


Figure 3

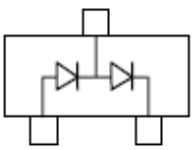


Figure 4

The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!